

278.

标题: THz/sub-THz direct detection detector on the basis of electron/hole heating in MCT layers

作者: Zabudsky, V (Zabudsky, V.); Sizov, F (Sizov, F.); Momot, N (Momot, N.); Tsybrii, Z (Tsybrii, Z.); Sakhno, N (Sakhno, N.); Bunchuk, S (Bunchuk, S.); Michailov, N (Michailov, N.); Varavin, V (Varavin, V.)

来源出版物: SEMICONDUCTOR SCIENCE AND TECHNOLOGY 卷: 27 期: 4 文献号: 045002 DOI: 10.1088/0268-1242/27/4/045002 出版年: APR 2012

在 Web of Science 中的被引频次: 0

被引频次合计: 0

引用的参考文献数: 11

摘要: Direct detection thin-film bipolar narrow-gap Hg<sub>1-x</sub>Cd<sub>x</sub>Te semiconductor is considered as a waveguide THz/sub-THz bolometer. The response of such thin layer detectors was calculated and measured in the  $\nu = 0.037$ -1.54 THz frequency range at T similar to 70-300 K. Noise equivalent power of such detectors can reach NEP<sub>300</sub> (K) similar to  $4 \times 10^{(-10)}$  W Hz<sup>(-1/2)</sup> and NEP<sub>100</sub> (K) similar to  $10^{(-11)}$  in the low-frequency part of the sub-THz spectral range.

入藏号: WOS:000301883000003

语种: English

文献类型: Article

KeyWords Plus: BOLOMETER; TEMPERATURE

地址: [Zabudsky, V.; Sizov, F.; Momot, N.; Tsybrii, Z.; Sakhno, N.; Bunchuk, S.] Inst Semicond Phys NASU, UA-03028 Kiev, Ukraine

[Michailov, N.; Varavin, V.] Inst Semicond Phys SB RAS, Novosibirsk 630090, Russia

通讯作者地址: Zabudsky, V (通讯作者), Inst Semicond Phys NASU, Nauki Av 41, UA-03028 Kiev, Ukraine

电子邮件地址: zvv1968@yahoo.com

出版商: IOP PUBLISHING LTD

出版商地址: TEMPLE CIRCUS, TEMPLE WAY, BRISTOL BS1 6BE, ENGLAND

Web of Science 分类: Engineering, Electrical & Electronic; Materials Science, Multidisciplinary; Physics, Condensed Matter

学科类别: Engineering; Materials Science; Physics

IDS 号: 913MV

ISSN: 0268-1242

29 字符的来源出版物名称缩写: SEMICOND SCI TECH

ISO 来源出版物缩写: Semicond. Sci. Technol.

来源出版物页码计数: 8